Quad 2-Channel Multiplexer

The MC74VHC157 is an advanced high-speed CMOS quad 2-channel multiplexer, fabricated with silicon gate CMOS technology. It achieves high-speed operation similar to equivalent Bipolar-Schottky TTL, while maintaining CMOS low-power dissipation.

It consists of four 2-input digital multiplexers with common select (S) and enable (\overline{E}) inputs. When \overline{E} is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 4.1 \text{ ns (Typ)}$ at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 82 FETs
- These Devices are Pb-Free and are RoHS Compliant

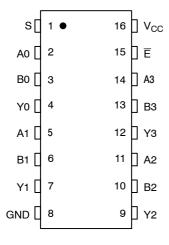


Figure 1. Pin Assignment



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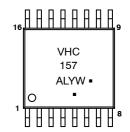
MARKING DIAGRAMS







CASE 948F



VHC157 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MC74VHC157DR2G	SOIC-16	2500 Units/Reel
MC74VHC157DTR2G	TSSOP-16	2500 Units/Reel

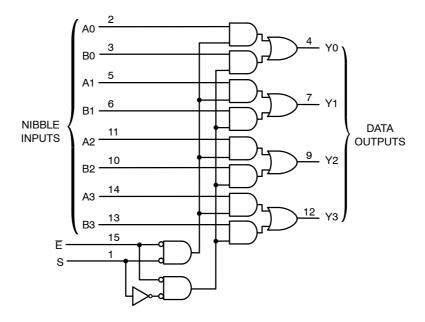


Figure 2. Expanded Logic Diagram

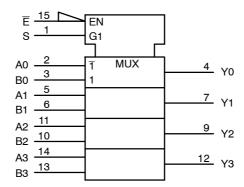


Figure 3. IEC Logic Symbol

FUNCTION TABLE

Inp	Outputs	
Ē	Y0 – Y3	
Н	Х	L
L	L	A0-A3
L	Н	B0-B3

A0 – A3, B0 – B3 = the levels of the respective Data–Word Inputs.

MAXIMUM RATINGS (Note 1)

Symbol	Paramet	Value	Unit	
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		-0.5 to $V_{CC} + 7.0$	V
V _O	DC Output Voltage		-0.5 to $V_{CC} + 7.0$	V
I _{IK}	DC Input Diode Current	V _I < GND	-20	mA
I _{OK}	DC Output Diode Current	V _O < GND	±20	mA
I _O	DC Output Sink Current		±25	mA
I _{CC}	DC Supply Current per Supply Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Se	econds	260	°C
TJ	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance		250	°C/W
P_{D}	Power Dissipation in Still Air at 85°C		250	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% - 35%	UL-94-VO (0.125 in)	
V _{ESD}	ESD Withstand Voltage	>2000 >200 N/A	V	
I _{Latch-Up}	Latch-Up Performance Above	V _{CC} and Below GND at 85°C (Note 5)	±500	mA

Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these
conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum-rated
conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{IN}	DC Input Voltage (Note 6)	0	5.5	V
V _{OUT}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature Range, all Package Types	- 55	125	°C
t _r , t _f	Input Rise or Fall Time $ \begin{array}{c} V_{CC} = 3.3 \ V \ \pm \ 0.3 \ V \\ V_{CC} = 5.0 \ V \ \pm \ 0.5 \ V \end{array} $	0 0	100 20	ns/V

^{6.} Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

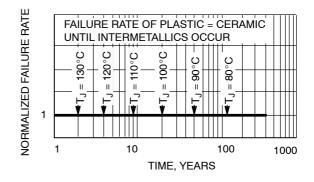


Figure 4. Failure Rate vs. Time Junction Temperature

^{2.} Tested to EIA/JESD22-A114-A.

^{3.} Tested to EIA/JESD22-A115-A.

^{4.} Tested to JESD22-C101-A.

^{5.} Tested to EIA/JESD78.

DC CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	Т	A = 25°	2	T _A ≤	85°C	-55°C ≤T	_ _A ≤125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 to 5.5	1.5 0.7 V _{CC}			1.5 0.7 V _{CC}		1.5 0.7 V _{CC}		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 to 5.5			0.5 0.3 V _{CC}		0.5 0.3 V _{CC}		0.5 0.3 V _{CC}	V
V _{OH}	High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.8		2.34 3.66		
V _{OL}	Low-Level Output Voltage	$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = 4$ mA $I_{OH} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			± 0.1		±1.0		±1.0	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			4.0		40.0		40.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input t_{r} = t_{f} = 3.0 ns)

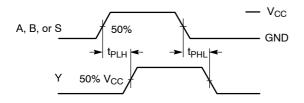
					T _A = 25°	С	T _A ≤	85°C	–55°C ≤T	A ≤ 125°C	
Symbol	Characteristic	Test Condit	ions	Min	Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay, A to B to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		6.2 8.7	9.7 13.2	1.0 1.0	11.5 15.0	1.0 1.0	11.5 15.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		4.1 5.6	6.4 8.4	1.0 1.0	7.5 9.5	1.0 1.0	7.5 9.5	
t _{PLH} , t _{PHL}	Propagation Delay, S to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		8.4 10.9	13.2 16.7	1.0 1.0	15.5 19.0	1.0 1.0	15.5 19.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		5.3 6.8	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	
t _{PLH} , t _{PHL}	Propagation Delay, E to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		8.7 11.2	13.6 17.1	1.0 1.0	16.0 19.5	1.0 1.0	16.0 19.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		5.6 7.1	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	
C _{IN}	Input Capacitance				4	10		10		10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 7)	20	pF

^{7.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption: $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}; C_L = 50 \text{ pF}; V_{CC} = 5.0 \text{ V})$

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V



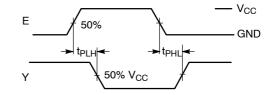
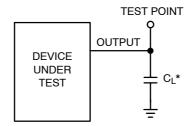


Figure 5. Switching Waveform

Figure 6. Inverting Switching



^{*}Includes all probe and jig capacitance.

Figure 7. Test Circuit

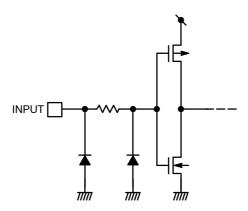


Figure 8. Input Equivalent Circuit





SOIC-16 CASE 751B-05 **ISSUE K**

DATE 29 DEC 2006

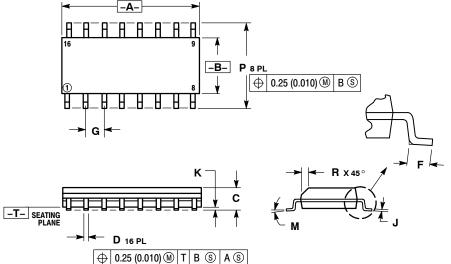
- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD ENGREPHING.
- - PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



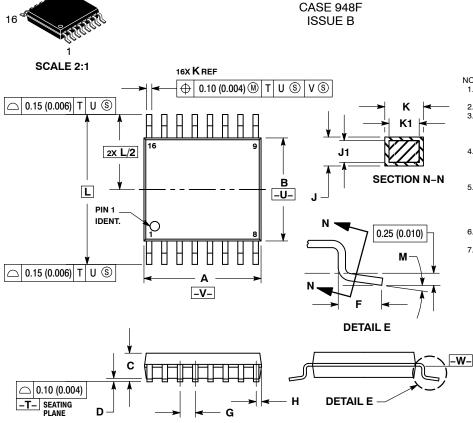
2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION	2. 3. 4. 5. 6. 7. 8. 9. 10.	CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION ANODE CATHODE CATHODE ANODE NO CONNECTION		COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #3 BASE, #3 EMITTER, #3	2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 EMITTER, #4 BASE, #4 BASE, #4 BASE, #3		
12.	EMITTER		CATHODE	12.	COLLECTOR, #3	12.		DECOM	MENDED
13. 14.	BASE COLLECTOR		CATHODE NO CONNECTION	13. 14.	COLLECTOR, #4 BASE, #4	13.	BASE, #2 EMITTER, #2		
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1	SOLDERING	FOOTPRINT*
16.	COLLECTOR		CATHODE	16.	COLLECTOR, #4		EMITTER, #1	g	×
									40
STYLE 5:		STYLE 6:		STYLE 7:				0.	70 7
	DRAIN, DYE #1		CATHODE		SOURCE N-CH			1	ı6X 1.12 < ➤
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPU	T)		<u> </u>	<u> </u>
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPU		1	□ 1	16
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	.,	*	_	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)			
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU	T)	16X		
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU	T)	0.58 ^{_1}		
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH			—	
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU		_	<u> </u>	
11.	GATE, #3		ANODE	11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3			12.	COMMON DRAIN (OUTPU	T)			
13.	GATE, #2		ANODE	13.	GATE N-CH				
14.	SOURCE, #2		ANODE	14.	COMMON DRAIN (OUTPU			Ш .	
15.	GATE, #1		ANODE	15.	COMMON DRAIN (OUTPU	T)			PITCH
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH			ш	
								8	9

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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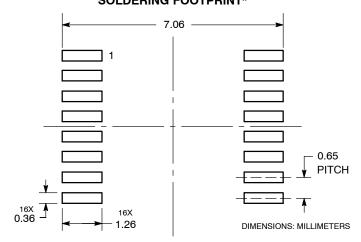
DATE 19 OCT 2006

NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABILE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	٥°	8 °	0 °	8 °

RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week

G or • = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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